FM60H100K/X

60V N-channel MOSFET

- N-Channel: 60V 100A
- RDS(on)Typ= 3.8mΩ@VGS = 10V
- Very Low On-resistance RDS(ON)
- LowCrss
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Application

- PWM Application
- Load Switch

Package



TO-252top view



Marking and pin assignment

试用水印 www.superchip.cn

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-Source Voltage	60	V
I_D	Drain Current - Continuous (TC = 25℃)	100	A
	- Continuous (TC = 100℃)	62	A
I_{DM}	Drain Current - Pulsed (Note 1)	380	A
V_{GSS}	Gate-Source Voltage	±20	V
E_{AS}	Single Pulsed Avalanche Energy	625	mJ
P_D	Power Dissipation (TC = 25℃)	92	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.35	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	℃
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	-55 to +150	℃